

SEMiX[®]

IGBT Modules & Bridge Rectifier Family

Technical Explanations

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Martin May

Content

1	Type Designation System.....	3
2	Disclaimer.....	3

1 Type Designation System

1	2	3	4	5	6	7
SEMiX	45	2	GB	12	6	HDs

1 SEMiX: Product name

2 Rated output current $I_C/10$ (For product lines "126", "12E4", "176")
 Nominal chip current $I_{C,nom}/10$ (For product line "066")
 Rated output current $I_{FAV}, I_{FAV}, I_D/10$ (For rectifier modules)

3 Housing size

1	=	1, 1s, 13
2	=	2, 2s
3	=	3, 3s, 33c
4	=	4, 4s

4 Circuit specification (examples)

GB	=	IGBT half bridge
GAL	=	IGBT low side chopper
GAR	=	IGBT high side chopper
GD	=	3 ~ IGBT inverter, "six-pack"
KD	=	Diode rectifier half bridge
KH	=	Half controlled rectifier half bridge
KT	=	Controlled rectifier half bridge
D	=	3 ~ rectifier bridge not controlled
DH	=	3 ~ rectifier bridge half controlled

5 Voltage class

06	=	600 V
12	=	1200 V
16	=	1600 V (rectifier only)
17	=	1700 V

6 IGBT chip technology

6	=	Trench IGBT3 (600 V, 1200V and 1700 V)
E4	=	Trench IGBT4 (1200 V)

7 Appendix (optional)

D	=	CAL Diode
HD	=	CAL HD Diode
s	=	Spring pin version of housing
c	=	Six-pack comparable with competitors
v1, v2,...	=	Exclusive, customised special version

2 Disclaimer

The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.